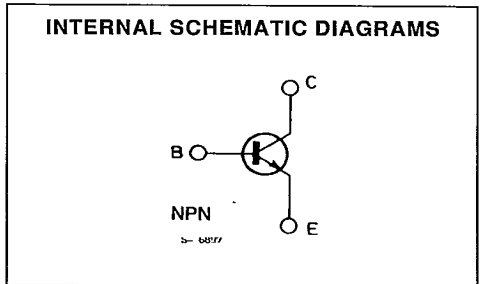
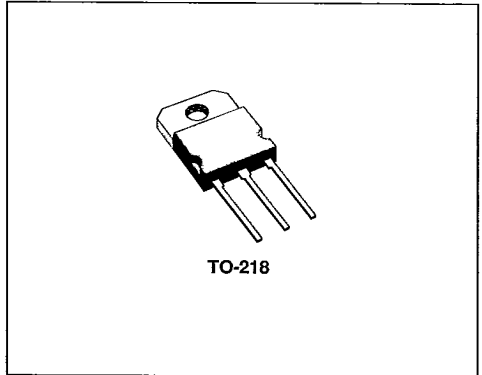


DESCRIPTION

The BU426 and BU426A are silicon multiepitaxial mesa NPN transistors in SOT-93 plastic package, particularly intended for switch-mode CTV supply systems.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BU426	BU426A	
V _{CES}	Collector-emitter Voltage (V _{BE} = 0)	800	900	V
V _{CEO}	Collector-emitter Voltage (I _B = 0)	375	400	V
V _{EBO}	Emitter-base Voltage (I _C = 0)	10		V
I _C	Collector-current	6		A
I _{CM}	Collector-peak Current (t _p = 2 ms)	8		A
I _B	Base Current	3		A
P _{tot}	Total Power Dissipation at T _{case} ≤ 25 °C	113		W
T _{stg}	Storage Temperature	- 65 to 150		°C
T _j	Junction Temperature	150		°C

Thermal DATA

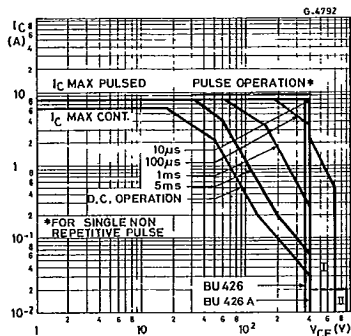
R _{thj-case}	Thermal Resistance Junction-case	Max	1.1	°C/W
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ELECTRICAL CHARACTERISTICS(T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cutoff Current (V _{BE} = 0)	for BU426 V _{CE} = 800 V for BU426A V _{CE} = 900 V T _{case} = 125 °C for BU426 V _{CE} = 800 V for BU426A V _{CE} = 900 V			1 1 2 2	mA mA mA mA
I _{EBO}	Emitter Cutoff Current (I _C = 0)	V _{EB} = 10 V			10	mA
V _{CE0(sus)} *	Collector-emitter Sustaining Voltage (I _B = 0)	for BU426 I _C = 100 mA for BU426A I _C = 100 mA	375 400			V V
V _{CE(sat)} *	Collector-emitter Saturation Voltage	I _C = 2.5 A I _B = 0.5 A I _C = 4 A I _B = 1.25 A			1.5 3	V V
V _{BE(sat)} *	Base-emitter Saturation Voltage	I _C = 2.5 A I _B = 0.5 A I _C = 4 A I _B = 1.25 A			1.4 1.6	V V
h _{FE} *	DC Current Gain	I _C = 0.6 A V _{CE} = 5 V		30	60	
t _{on}	Turn-on Time	I _C = 2.5 A I _{B1} = 0.5 A I _{B1} = 0.5 A V _{CC} = 250 V		0.25	0.5	µs
t _s	Storage Time	I _C = 2.5 A I _{B1} = 0.5 A		2.5	3.5	µs
t _f	Fall Time	I _{B2} = -1 A V _{CC} = 250 V		0.2	0.5	µs
t _f	Fall Time	I _C = 2.5 A I _{B2} = -1 A T _{case} = 100 °C V _{CC} = 250 V			0.75	µs

* Pulsed : pulse duration = 300 µs, duty cycle = 1.5 %.

Safe Operating Areas.



I = Area of permissible operation driving turn-on provided R_{BE} = 100Ω and t_p ≤ 0.6µs.
 II = Area of permissible operation with V_{BE} ≤ 0 ; t_p ≤ 2µs.